

Supplemental information

Optimization of Triazine-Based Acceptor (CN-T2T) as Electron Transport Layers for Highly Efficient Near-Infrared Perovskite Light-Emitting Diodes

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Supplemental Information

Supplemental Figures

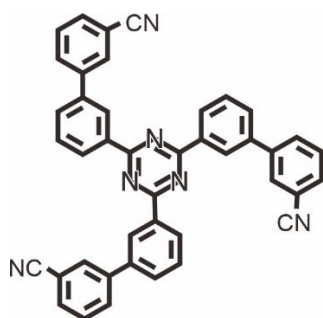


Figure S1. Structural formula of the CN-T2T molecule

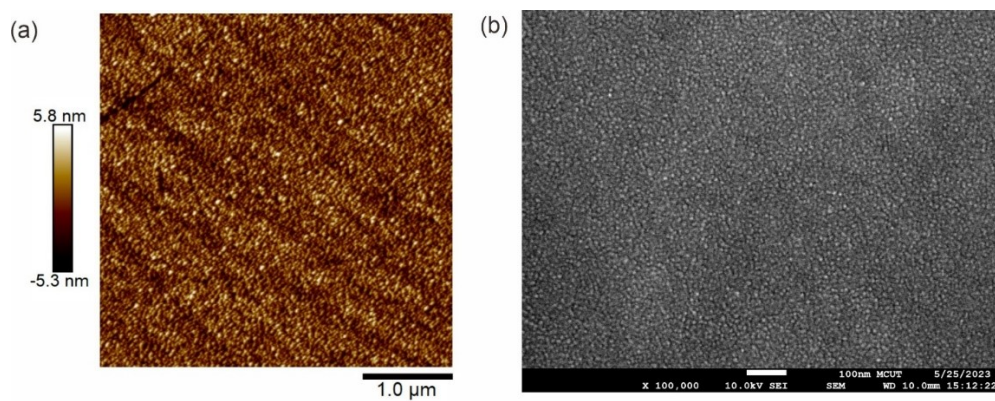


Figure S2. (a) SEM and (b) AFM characterizations on the top surface of CN-T2T

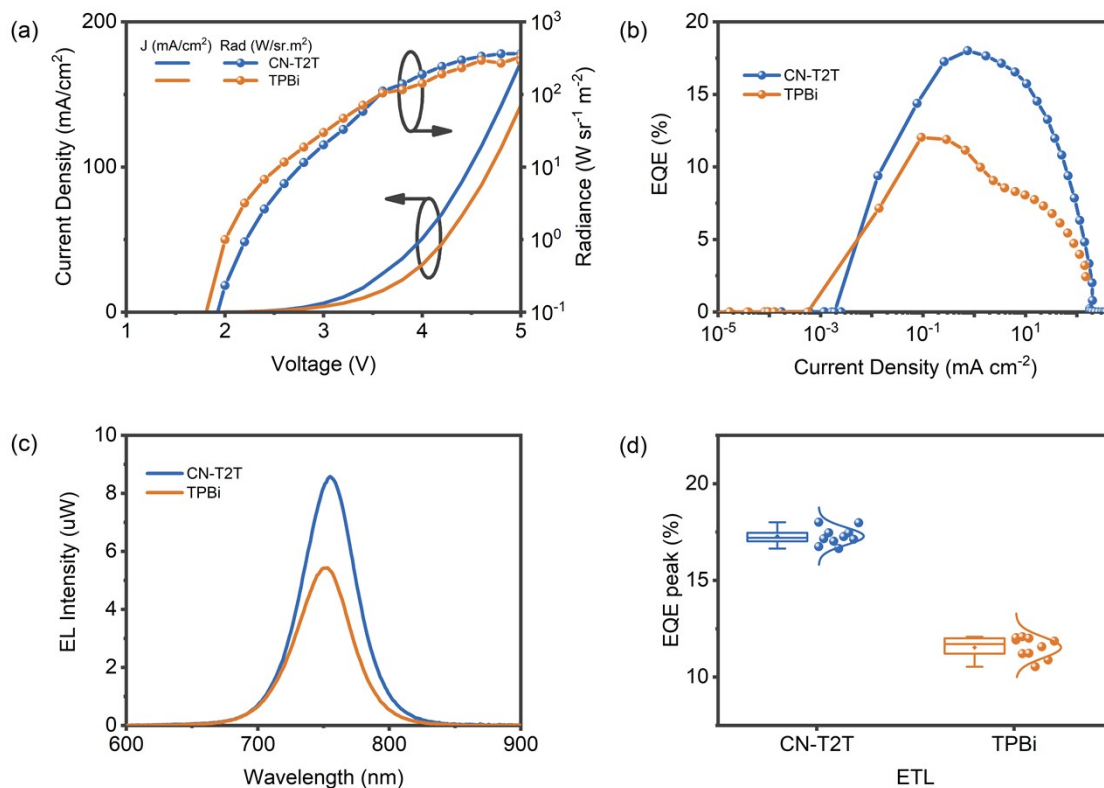


Figure S3. Comparison of MAPbI₃ perovskite led with CN-T2T and TPBi as ETL a) Current density–voltage–luminance (J-V-L), (b) EQE–Current density plots, (c) EL spectra of NIR PeLEDs (d) The statistical data of EQE peaks.

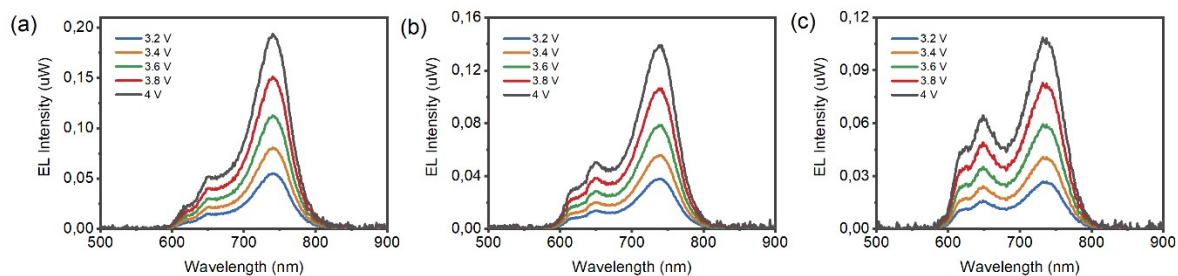


Figure S4. voltage dependent EL spectra variations of the NIR PeLED with PEAPbI_{3-x}Br_x sensing layer under different thickness of CN-T2T, (a) 30 nm, (b) 50 nm, and (c) 70 nm.

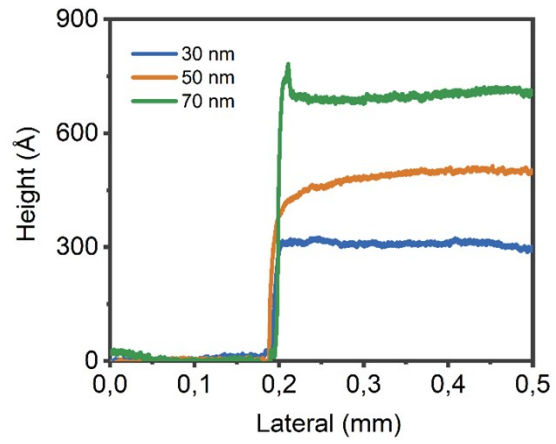


Figure S5. CN-T2T thickness measurements performed by stylus profilometer (Bruker DektakXT)